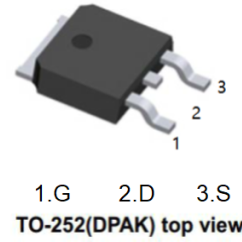


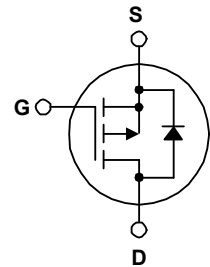
Description

This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.



Features

- $V_{DS} (V) = -60V$
- $I_D = -12A$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 135m\Omega$ ($V_{GS} = -10V$)



Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted.

Symbol	Parameter	FQD17P06 / FQU17P06	Unit
V_{DSS}	Drain-Source Voltage	-60	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ C$)	-12
		- Continuous ($T_C = 100^\circ C$)	-7.6
I_{DM}	Drain Current	- Pulsed (Note 1)	-48
V_{GSS}	Gate-Source Voltage	± 25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	300	mJ
I_{AR}	Avalanche Current (Note 1)	-12	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	4.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-7.0	V/ns
P_D	Power Dissipation ($T_A = 25^\circ C$) *	2.5	W
	Power Dissipation ($T_C = 25^\circ C$)	44	W
	- Derate above $25^\circ C$	0.35	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds.	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	FQD17P06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.85	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-0.06		V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -48\text{ V}, T_C = 125^\circ\text{C}$			-10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$			100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1.1	-2	-3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -6.0\text{ A}$		110	135	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = -30\text{ V}, I_D = -6.0\text{ A}$		8.7		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		690	900	pF
C_{oss}	Output Capacitance			325	420	pF
C_{rss}	Reverse Transfer Capacitance			80	105	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -30\text{ V}, I_D = -8.5\text{ A},$ $R_G = 25\ \Omega$		13	35	ns
t_r	Turn-On Rise Time			100	210	ns
$t_{d(off)}$	Turn-Off Delay Time			22	55	ns
t_f	Turn-Off Fall Time		(Note 4)	60	130	ns
Q_g	Total Gate Charge	$V_{DS} = -48\text{ V}, I_D = -17\text{ A},$ $V_{GS} = -10\text{ V}$		21	27	nC
Q_{gs}	Gate-Source Charge			4.2		nC
Q_{gd}	Gate-Drain Charge		(Note 4)	10		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current				-12	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current				-48	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -12\text{ A}$			-4.0	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -17\text{ A},$		92		ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$		0.32		μC

NOTES:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 2.4\text{ mH}, I_{AS} = -12\text{ A}, V_{DD} = -25\text{ V}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq -17\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

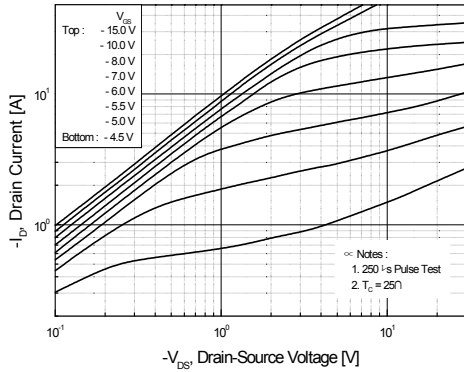


Figure 1. On-Region Characteristics

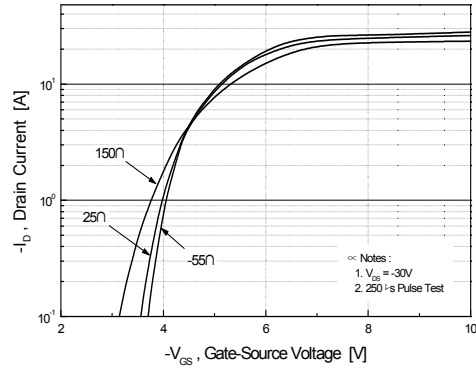


Figure 2. Transfer Characteristics

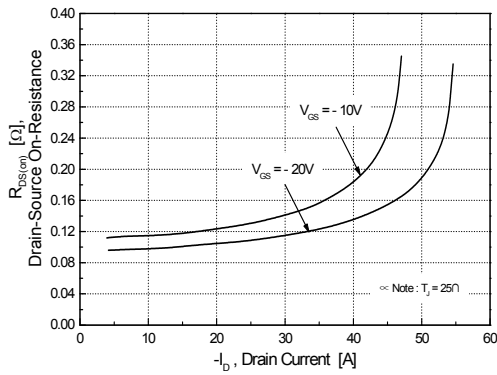


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

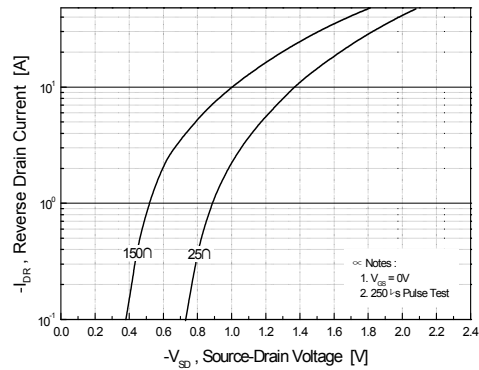


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

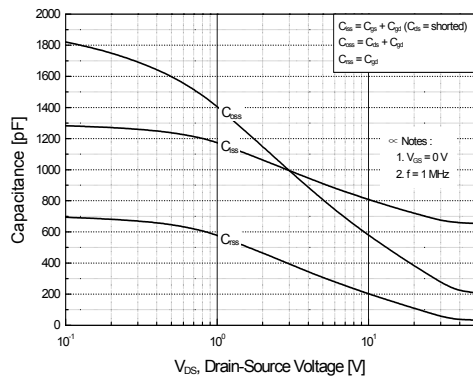


Figure 5. Capacitance Characteristics

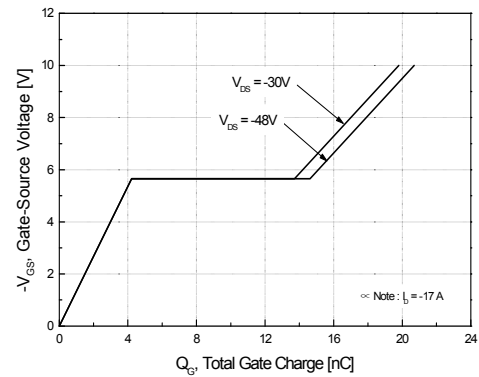


Figure 6. Gate Charge Characteristics

Typical Performance Characteristics

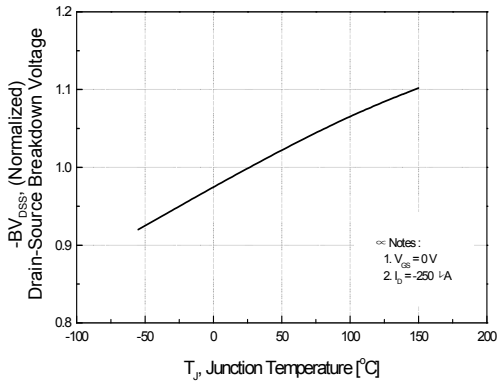


Figure 7. Breakdown Voltage Variation vs. Temperature

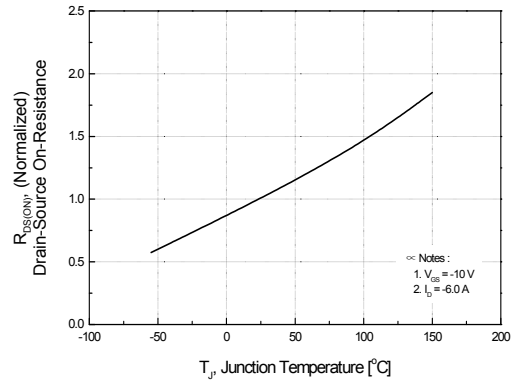


Figure 8. On-Resistance Variation vs. Temperature

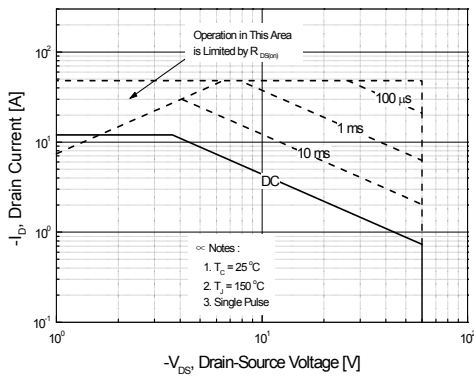


Figure 9. Maximum Safe Operating Area

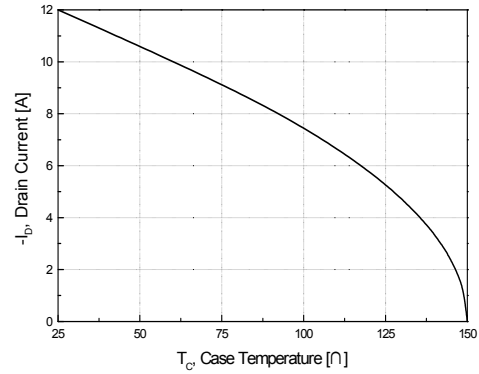


Figure 10. Maximum Drain Current vs. Case Temperature

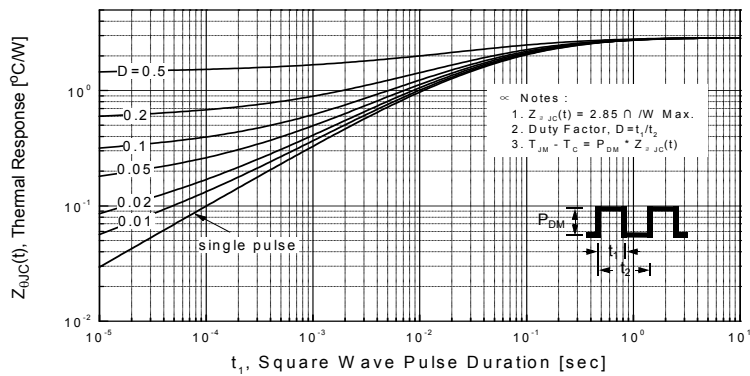


Figure 11. Transient Thermal Response Curve

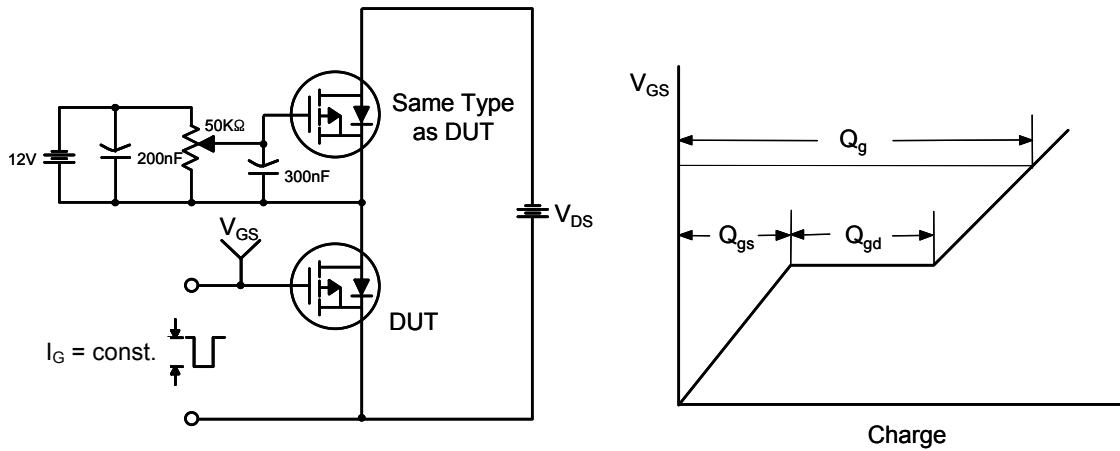


Figure 12. Gate Charge Test Circuit & Waveform

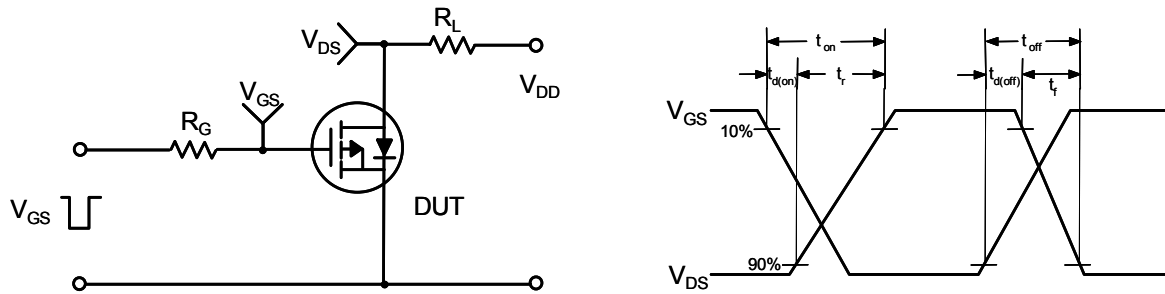


Figure 13. Resistive Switching Test Circuit & Waveforms

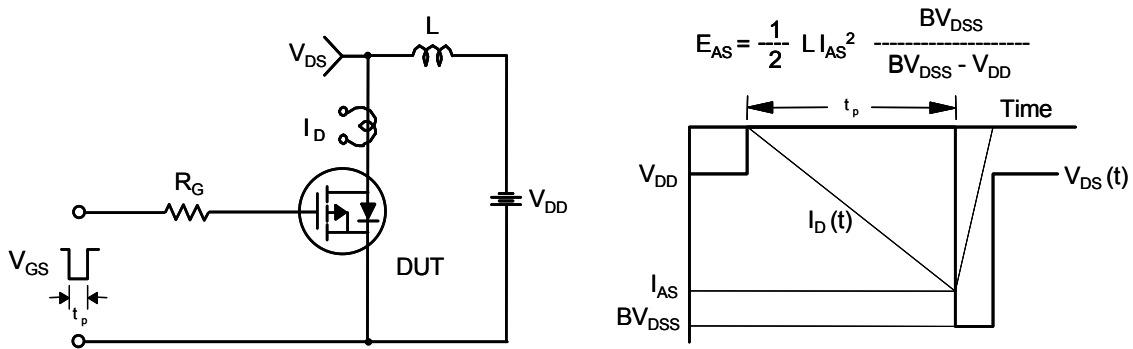


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

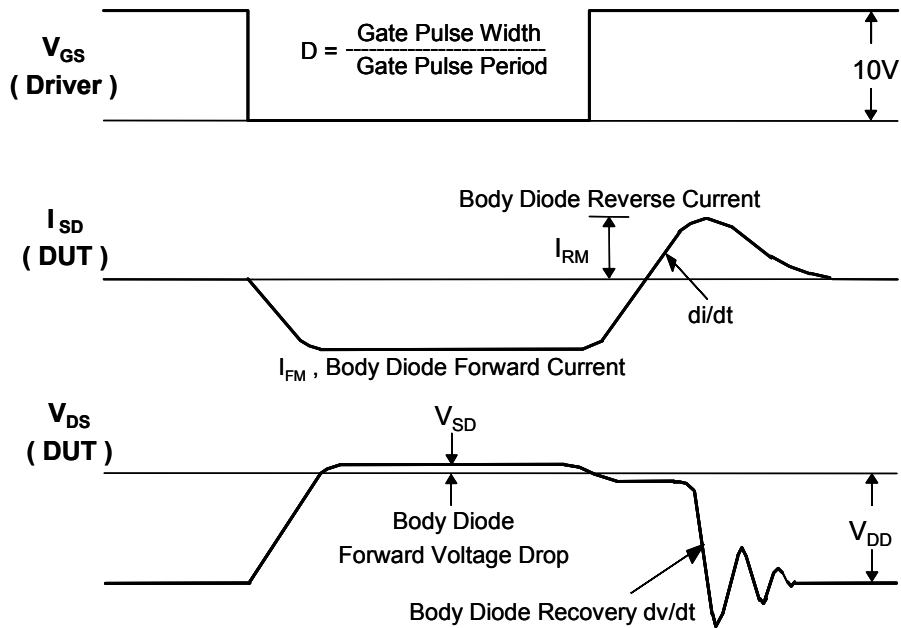
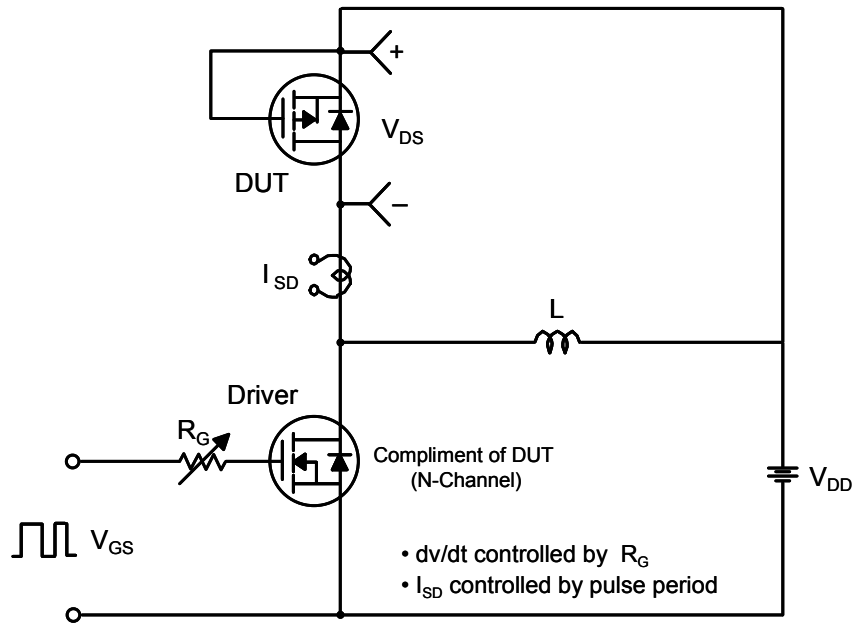
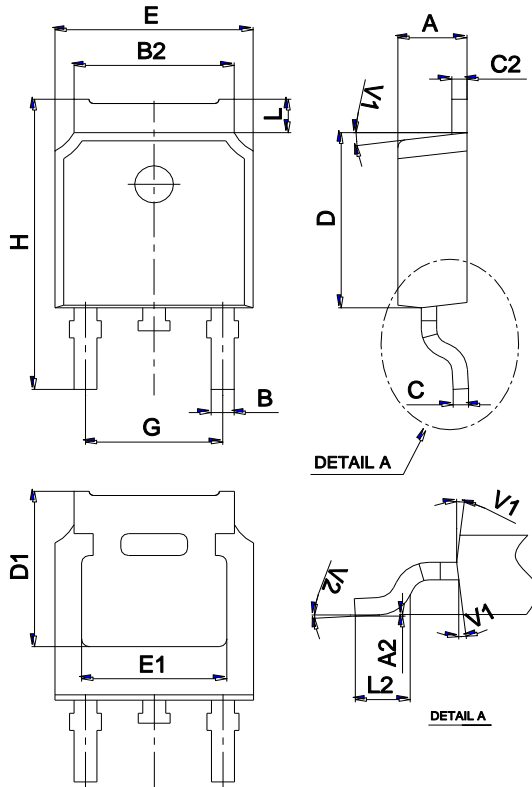


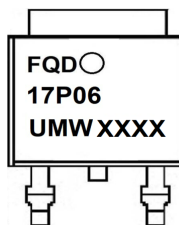
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMWFQD17P06TM	TO-252	2500	Tape and reel